

# isc N-Channel MOSFET Transistor

# IPD50R950CE,IIPD50R950CE

#### • FEATURES

- Static drain-source on-resistance:
  R<sub>DS</sub>(on)≤0.95Ω
- Enhancement mode:
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

- · Fast switching
- · Very high commutation ruggedness

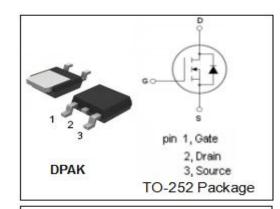


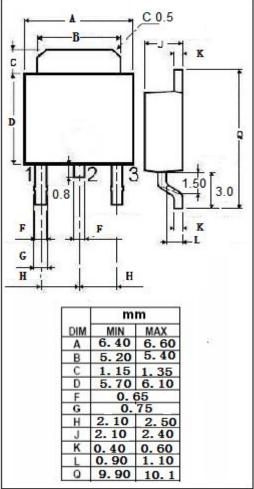
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{ extsf{DSS}}$	Drain-Source Voltage	500	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
l <sub>D</sub>	Drain Current-Continuous	6.6	A	
I <sub>DM</sub>	Drain Current-Single Pulsed	12.8	А	
$P_D$	Total Dissipation @T <sub>C</sub> =25℃	53	W	
Tj	Max. Operating Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature -55~150		$^{\circ}$	

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	2.35	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT				
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =1mA	500			V				
V <sub>GS(th)</sub>	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> =0.1mA	2.5		3.5	V				
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =13V; I <sub>D</sub> =1.2A			0.95	Ω				
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = 20V;V <sub>DS</sub> =0V			0.1	μА				
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =500V; V <sub>GS</sub> = 0V			1	μА				
$V_{SD}$	Diode forward voltage	I <sub>F</sub> =1.6A, V <sub>GS</sub> = 0V		0.83		V				

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